

## N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)(Typ.)$	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
30	2.8 at V <sub>GS</sub> = 10 V	25	65.7 nC			
30	4 at V <sub>GS</sub> = 4.5 V	25				

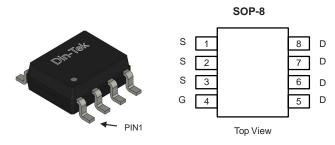
#### **FEATURES**

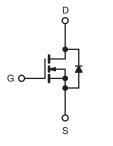
- DT-Trench Power MOSFET
- 100% Rg Tested
- RoHS Compliant

#### **APPLICATIONS**

Notebook CPU Core
-High-Side Switch







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V <sub>DS</sub>	30	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	V		
Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	_	25		
Continuous Diam Current (1) = 130 C)	T <sub>A</sub> = 100 °C	- I <sub>D</sub>	19		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	100	A		
Single Pulse Avalanche Current	IAS	36			
Single Avalanche Energy	E <sub>AS</sub>	315	mJ		
Maximum Daylar Dissipation(	T <sub>A</sub> = 25 °C	Б	3.2	W	
Maximum Power Dissipation <sup>c</sup>	T <sub>A</sub> = 100 °C	- P <sub>D</sub>	1.3	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) <sup>d</sup>	R <sub>thJA</sub>	39	°C/W		

#### **Notes**

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	-	2.2	7 v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 30  V,  V_{GS} = 0  V$	-	-	1	μА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	-	-	10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	25	-	-	Α	
Paris Course On Otata Basista	D	$V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	2.8	3.5	m0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A	-	4	5	mΩ	
Forward Transconductance <sup>a</sup>	9fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	-	95	-	S	
Dynamic <sup>b</sup>				<u> </u>			
Input Capacitance	C <sub>iss</sub>		-	3200	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	473	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	441	-		
Total Gate Charge <sup>c</sup>	Qg		-	65.7	-		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	5.1	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	13.4	-		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	-	2	-	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	8	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, I_D = 10 \text{ A}, R_g = 1 \Omega$	-	10	-		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$V_{GS}$ = 10 V , $R_L$ = 1.5 $\Omega$	-	16	-	ns -	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	9	-		
<b>Drain-Source Body Diode Ratings and</b>	Characterist	ics <sup>b</sup> (T <sub>J</sub> = 25 °C)	<u> </u>	•			
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>A</sub> = 25 °C	-	-	25	Α	
Pulsed Current	I <sub>SM</sub>		-	-	100	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 1 A, V <sub>GS</sub> = 0 V	-	0.6	-	V	
Reverse Recovery Time	t <sub>rr</sub>	L = 10 A di/dt = 100 A/v;	-	14	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 10 \text{ A}, \text{ di/dt } = 100 \text{ A/}\mu\text{s}$	-	5	-	nC	

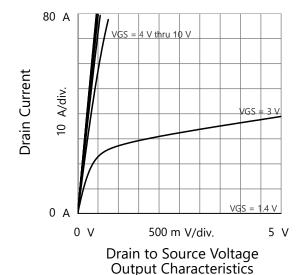
#### Notes

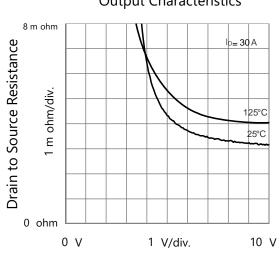
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

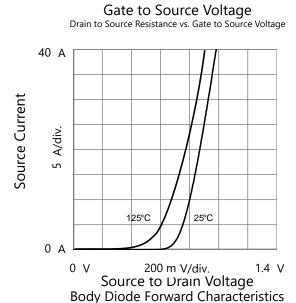
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.

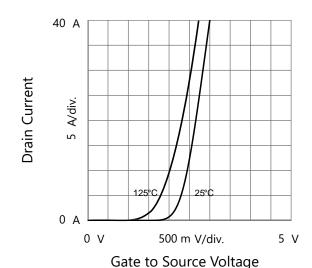


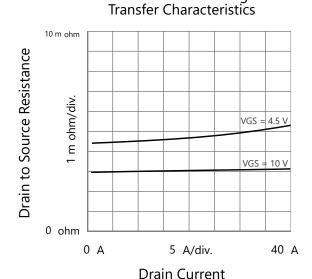
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

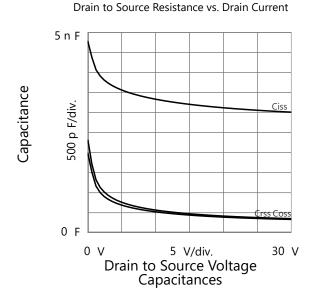






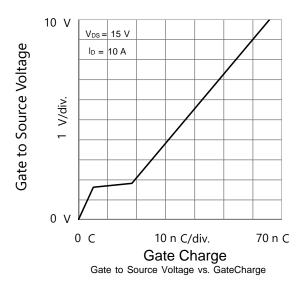


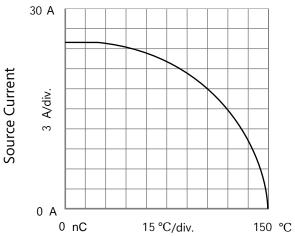




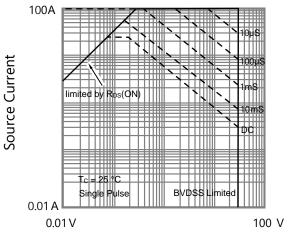


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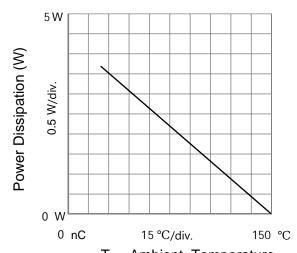




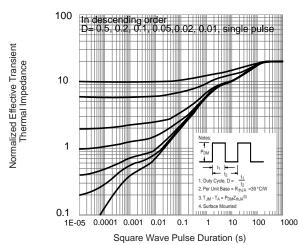
T<sub>A</sub> - Ambient Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Case



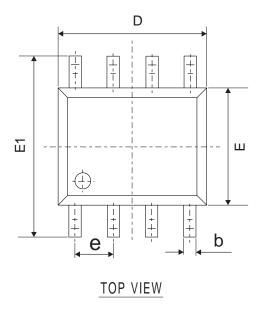
T<sub>A</sub> - Ambient Temperature

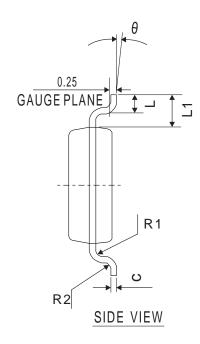


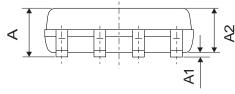
Normalized Thermal Transient Impedance, Junction-to-Ambient



# SOP-8 PACKAGE OUTLINE







SIDE VIEW

## **COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX
Α	1.30	1.60	1.85
A1	0.03	0.15	0.28
A2	1.20	1.45	1.70
b	0.26	0.40	0.54
С	0.132	0.203	0.273
D	4.50	4.90	5.30
Е	3.50	3.00	4.30
E1	5.50	6.00	6.50
L	0.30	0.70	1.10
θ	2°	4°	6°
L1	1.04REF		
е	1.27BSC		
R1	0.07TYP		
R2	0.07TYP		





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